

2SK1621 L, 2SK1621 S

Silicon N-Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter and motor driver

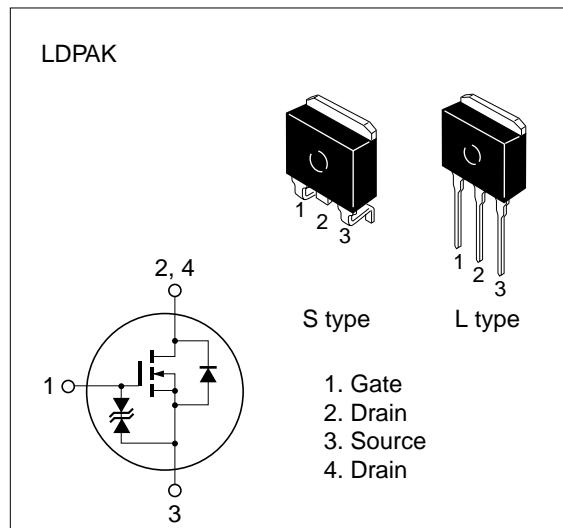


Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	7	A
Drain peak current	I _{D(pulse)} *	28	A
Body to drain diode reverse drain current	I _{DR}	7	A
Channel dissipation	P _{ch} **	50	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 µs, duty cycle ≤ 1 %

** Value at T_C = 25 °C

2SK1621 (L), 2SK1621 (S)

Table 2 Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR)DSS}	250	—	—	V	I _D = 10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR)GSS}	±20	—	—	V	I _G = ±100 µA, V _{DS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	µA	V _{GS} = ±16 V, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	250	µA	V _{DS} = 200 V, V _{GS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2.0	—	4.0	V	I _D = 1 mA, V _{DS} = 10 V
Static Drain to source on state resistance	R _{DS(on)}	—	0.40	0.55	Ω	I _D = 4 A, V _{GS} = 10 V *
Forward transfer admittance	y _{fs}	2.7	4.5	—	S	I _D = 4 A, V _{DS} = 10 V *
Input capacitance	C _{iss}	—	820	—	pF	V _{DS} = 10 V, V _{GS} = 0,
Output capacitance	C _{oss}	—	370	—	pF	f = 1 MHz
Reverse transfer capacitance	C _{rss}	—	115	—	pF	
Turn-on delay time	t _{d(on)}	—	12	—	ns	I _D = 4 A, V _{GS} = 10 V,
Rise time	t _r	—	48	—	ns	R _L = 7.5 Ω
Turn-off delay time	t _{d(off)}	—	70	—	ns	
Fall time	t _f	—	50	—	ns	
Body to drain diode forward voltage	V _{DF}	—	1.2	—	V	I _F = 7 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	400	—	ns	I _F = 7 A, V _{GS} = 0, dI _F /dt = 50 A/µs

* Pulse Test

See characteristic curves of 2SK741.

